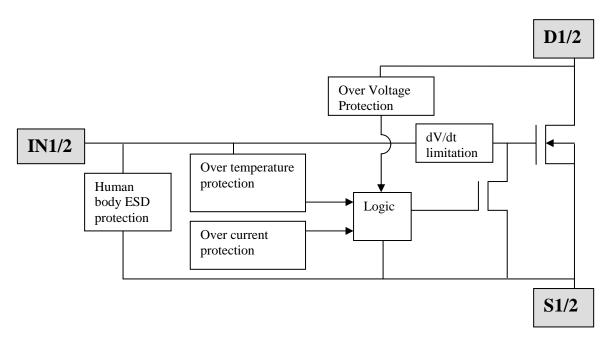


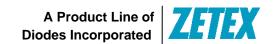
FUNCTIONAL BLOCK DIAGRAM



APPLICATIONS AND INFORMATION

- Two completely isolated independent channels
- Especially suited for loads with a high in-rush current such as lamps and motors.
- All types of resistive, inductive and capacitive loads in switching applications.
- μC compatible power switch for 12V and 24V DC applications.
- Automotive rated.
- Replaces electromechanical relays and discrete circuits.
- Linear Mode capability the current-limiting protection circuitry is designed to de-activate
 at low V_{DS} to minimise on state power dissipation. The maximum DC operating current is
 therefore determined by the thermal capability of the package/board combination, rather
 than by the protection circuitry. This does not compromise the product's ability to selfprotect at low V_{DS}.





ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--|---------------------|----------------------|-------|
| Continuous Drain-Source Voltage | V_{DS} | 60 | V |
| Drain-Source Voltage for short circuit protection | V _{DS(SC)} | 36 | V |
| Continuous Input Voltage | V_{IN} | -0.5 +6 | V |
| Continuous Input Current | I _{IN} | | mA |
| -0.2V≤V _{IN} ≤6V | | No limit | |
| V _{IN} <-0.2V or V _{IN} >6V | | I _{IN} ≤2 | |
| Operating Temperature Range | $T_j,$ | -40 to +150 | °C |
| Storage Temperature Range | T_{stg} | -55 to +150 | °C |
| Power Dissipation at T _A =25°C (a)(d) | P_D | 1.16 | W |
| Linear Derating Factor | | 9.28 | mW/°C |
| Power Dissipation at T _A =25°C (a)(e) | P_D | 1.67 | W |
| Linear Derating Factor | | 13.3 | mW/°C |
| Power Dissipation at T _A =25°C (b)(d) | P_D | 2.13 | W |
| Linear Derating Factor | | 17 | mW/°C |
| Pulsed Drain Current @ V _{IN} =3.3V (c) | I _{DM} | 2 | А |
| Pulsed Drain Current @ V _{IN} =5V (c) | I _{DM} | 2.5 | Α |
| Continuous Source Current (Body Diode) (a) | I _S | 1 | А |
| Pulsed Source Current (Body Diode) (c) | I _{SM} | 5 | А |
| Unclamped single pulse inductive energy, Tj=25°C, I_D =0.5A, V_{DD} =24V | E _{AS} | 210 | mJ |
| Electrostatic Discharge (Human Body Model) | V_{ESD} | 4000 | V |
| Charged Device Model | V_{CDM} | 1000 | V |

THERMAL RESISTANCE

| PARAMETER | SYMBOL | VALUE | UNIT |
|----------------------------|-----------------|-------|------|
| Junction to Ambient (a)(d) | $R_{\theta JA}$ | 108 | °C/W |
| Junction to Ambient (a)(e) | $R_{\theta JA}$ | 75 | °C/W |
| Junction to Ambient (b)(d) | $R_{\theta JA}$ | 58.7 | °C/W |
| Junction to Case (f) | $R_{	heta JC}$ | 26.5 | °C/W |

NOTES

- (a) For a dual device surface mounted on a 25mm x 25mm FR4 PCB single sided 1oz weight copper split down the middle on 1.6mm FR4 board, in still air conditions.
- (b) For a dual device surface mounted on FR4 PCB measured at t ≤ 10sec
- (c) Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300μs pulse width limited by junction temperature. Refer to transient Thermal Impedance Graph.
- (d) For a dual device with one active die.
- (e) For dual device with 2 active die running at equal power.
- (f) Thermal resistance from junction to solder-point (at the end of the drain lead)



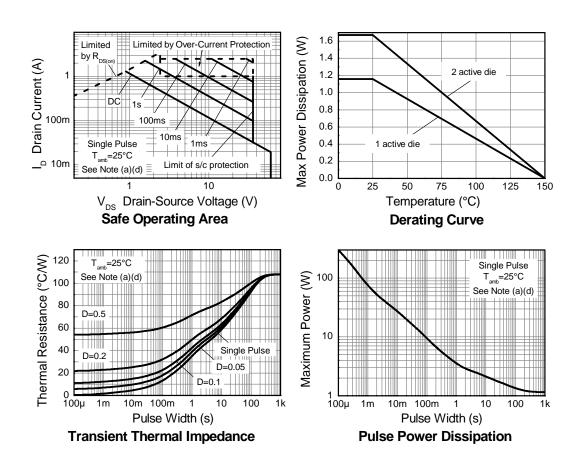


RECOMMENDED OPERATING CONDITIONS

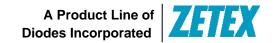
The ZXMS6004DT8 is optimised for use with μ C operating from 3.3V and 5V supplies.

| Symbol | Description | Min | Max | Units |
|----------|---|-----|-----|-------|
| V_{IN} | Input voltage range | 0 | 5.5 | V |
| T_A | Ambient temperature range | -40 | 125 | °C |
| V_{IH} | High level input voltage for MOSFET to be on | 3 | 5.5 | V |
| V_{IL} | Low level input voltage for MOSFET to be off | 0 | 0.7 | V |
| V_P | Peripheral supply voltage (voltage to which load is referred) | 0 | 36 | V |

CHARACTERISTICS







ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNIT | CONDITIONS | |
|---|---------------------|-----|-----|-----|------|---|--|
| Static Characteristics | | | | | | | |
| Drain-Source Clamp Voltage | $V_{DS(AZ)}$ | 60 | 65 | 70 | V | I _D =10mA | |
| Off state Drain Current | I _{DSS} | | | 500 | nA | V _{DS} =12V, V _{IN} =0V | |
| Off state Drain Current | I _{DSS} | | | 1 | uA | V_{DS} =36V, V_{IN} =0V | |
| Input Threshold Voltage | $V_{IN(th)}$ | 0.7 | 1 | 1.5 | V | $V_{DS}=V_{GS}$, $I_{D}=1$ mA | |
| Input Current | I _{IN} | | 60 | 100 | μΑ | V _{IN} =+3V | |
| Input Current | I _{IN} | | 120 | 200 | μΑ | V _{IN} =+5V | |
| Input Current while over temperature active | | | | 220 | μΑ | V _{IN} =+5V | |
| Static Drain-Source On-State Resistance | R _{DS(on)} | | 400 | 600 | mΩ | V_{IN} =+3 V , I_{D} =0.5 A | |
| Static Drain-Source On-State Resistance | R _{DS(on)} | | 350 | 500 | mΩ | V_{IN} =+5V, I_{D} =0.5A | |
| Continuous Drain Current (a)(e) | I _D | 0.9 | | | Α | V _{IN} =3V; T _A =25°C | |
| Continuous Drain Current (a)(e) | I _D | 1.0 | | | Α | V _{IN} =5V; T _A =25°C | |
| Continuous Drain Current (a)(d) | I _D | 1.1 | | | Α | V _{IN} =3V; T _A =25°C | |
| Continuous Drain Current (a)(d) | I _D | 1.2 | | | Α | V _{IN} =5V; T _A =25°C | |
| Current Limit (g) | I _{D(LIM)} | 0.7 | 1.7 | | Α | V _{IN} =+3V, | |
| Current Limit (g) | I _{D(LIM)} | 1 | 2.2 | | Α | V _{IN} =+5V | |
| Dynamic Characteristics | | | | | | | |
| Turn On Delay Time | t _{d(on)} | | 5 | | μS | V_{DD} =12V, I_{D} =0.5A, | |
| Rise time | t _r | | 10 | | μS | V _{GS} =5V | |
| Turn Off Delay Time | t _{d(off)} | | 45 | | μS | | |
| Fall Time | f _f | | 15 | | μS | | |

Notes:

(g) The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.



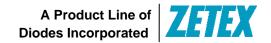


| PARAMETER | SYMBOL | MIN | TYP | MAX | UNIT | CONDITIONS |
|--|----------|-----|-----|-----|------|------------|
| Over-temperature Protection | | | | | | |
| Thermal Overload Trip Temperature (h) | T_{JT} | 150 | 175 | | °C | |
| Thermal hysteresis (h) | | | 10 | | °C | |

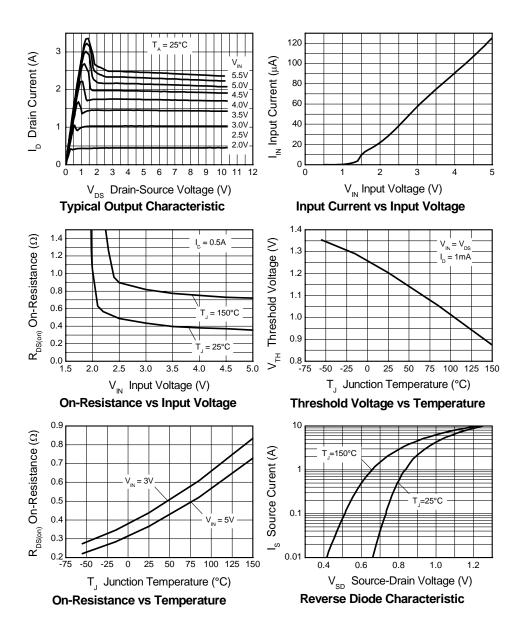
Note:

(h) Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods..

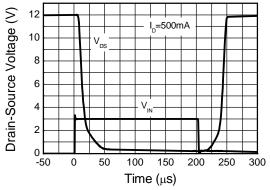


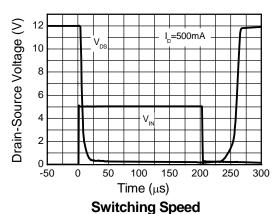


TYPICAL CHARACTERISTICS

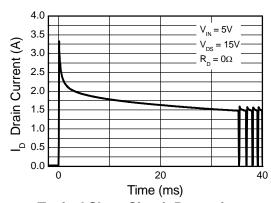






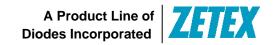


Switching Speed



Typical Short Circuit Protection





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